PD -95597

International
IOR Rectifier

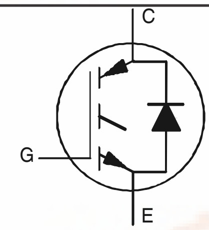
IRG4IBC30KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

- High switching speed optimized for up to 25kHz with low $V_{CE(on)}$
- Short Circuit Rating 10µs @ 125°C, V_{GE} = 15V
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220 FULLPAK
- Lead-Free



n-channel

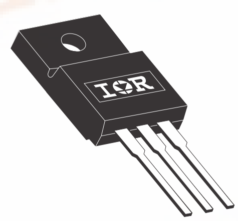
V_{CES} = 600V

$V_{CE(on)\ typ.}$ = 2.21V

@V_{GE} = 15V, I_C = 9.2A

Benefits

- Generation 4 IGBTs offer highest efficiencies available maximizing the power density of the system
- IGBT's optimized for specific application conditions
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise EMI
- Designed to exceed the power handling capability of equivalent industry-standard IGBT



TO-220 FULLPAK

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	17	A
I_C @ T_C = 100°C	Continuous Collector Current	9.2	A
I_{CM}	Pulsed Collector Current ①⑤	34	A
I_{LM}	Clamped Inductive Load Current ②⑤	34	A
I_F @ T_C = 100°C	Diode Continuous Forward Current	9.2	A
I_{FM}	Diode Maximum Forward Current	34	A
t_{sc}	Short Circuit Withstand Time	10	µs
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, t = 1 min	2500	V
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	45	W
P_D @ T_C = 100°C	Maximum Power Dissipation	18	W
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	°C
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case - IGBT	–––	2.8	°C/W
$R_{θCS}$	Junction-to-Case - Diode	–––	3.7	°C/W
$R_{θJA}$	Junction-to-Ambient, typical socket mount	–––	65	°C/W
Wt	Weight	2.0 (0.07)	–––	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	600	—	—	V	V_{GE} = 0V, I_C = 250µA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/°C	V_{GE} = 0V, I_C = 1.0mA	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.21	2.7	V	I_C = 16A	V_{GE} = 15V
		—	2.88	—		I_C = 28A	See Fig. 2, 5
		—	2.36	—		I_C = 16A, T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA	
g_{fe}	Forward Transconductance ④	5.4	8.1	—	S	V_{CE} = 100V, I_C = 16A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 600V	
		—	—	2500		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C	
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	I_C = 12A	See Fig. 13
		—	1.3	1.6		I_C = 12A, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions		
Q_g	Total Gate Charge (turn-on)	—	67	100	nC	I_C = 16A		
Q_{ge}	Gate - Emitter Charge (turn-on)	—	11	16		V_{CC} = 400V	See Fig.8	
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	37		V_{GE} = 15V		
$t_{d(on)}$	Turn-On Delay Time	—	60	—	ns			
t_r	Rise Time	—	42	—		T_J = 25°C		
$t_{d(off)}$	Turn-Off Delay Time	—	160	250		I_C = 16A, V_{CC} = 480V		
t_f	Fall Time	—	80	120		V_{GE} = 15V, R_G = 23Ω		
E_{on}	Turn-On Switching Loss	—	0.60	—	mJ	Energy losses include "tail"		
E_{off}	Turn-Off Switching Loss	—	0.58	—		and diode reverse recovery		
E_{ts}	Total Switching Loss	—	1.18	1.6		See Fig. 9,10,14		
t_{sc}	Short Circuit Withstand Time	10	—	—	µs	V_{CC} = 360V, T_J = 125°C		
						V_{GE} = 15V, R_G = 10Ω , V_{CPK} < 500V		
$t_{d(on)}$	Turn-On Delay Time	—	58	—	ns	T_J = 150°C,	See Fig. 10,11,18	
t_r	Rise Time	—	42	—		I_C = 16A, V_{CC} = 480V		
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		V_{GE} = 15V, R_G = 23Ω		
t_f	Fall Time	—	160	—		Energy losses include "tail"		
E_{ts}	Total Switching Loss	—	1.69	—	mJ	and diode reverse recovery		
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package		
C_{ies}	Input Capacitance	—	920	—	pF	V_{GE} = 0V		
C_{oes}	Output Capacitance	—	110	—		V_{CC} = 30V	See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	27	—		ƒ = 1.0MHz		
t_{rr}	Diode Reverse Recovery Time	—	42	60	ns	T_J = 25°C	See Fig.	
		—	80	120		T_J = 125°C	14	I_F = 12A
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	T_J = 25°C	See Fig.	
		—	5.6	10		T_J = 125°C	15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	80	180	nC	T_J = 25°C	See Fig.	
		—	220	600		T_J = 125°C	16	di/dt = 200Aµs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	—	180	—	A/µs	T_J = 25°C	See Fig.	
	During t_b	—	160	—		T_J = 125°C	17	

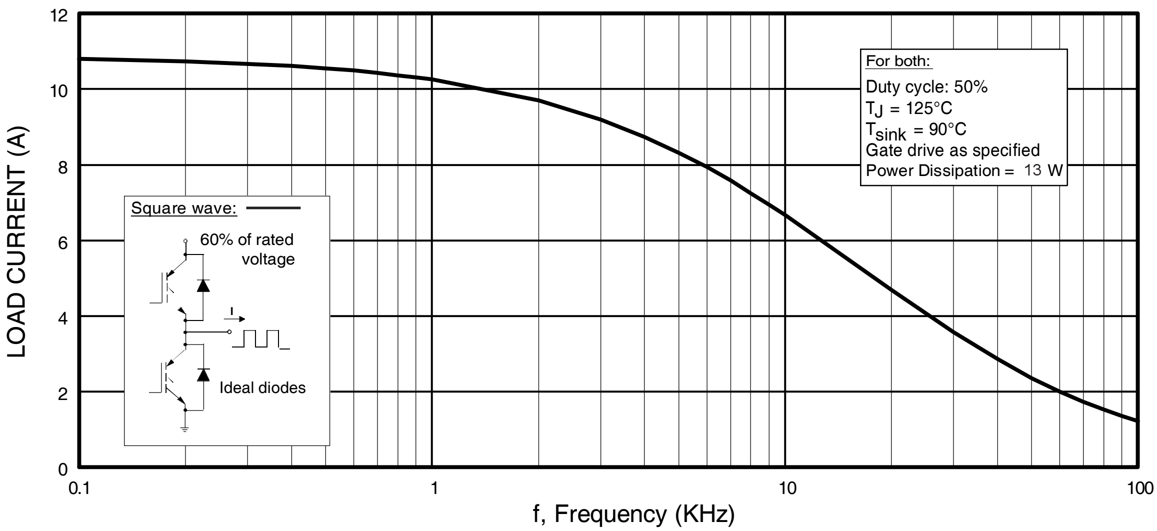


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

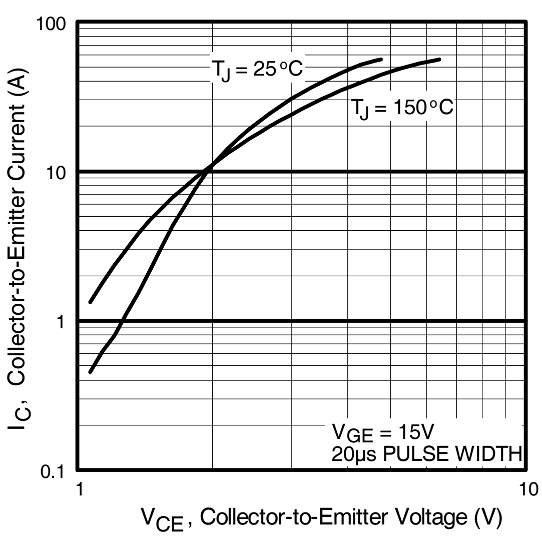


Fig. 2 - Typical Output Characteristics

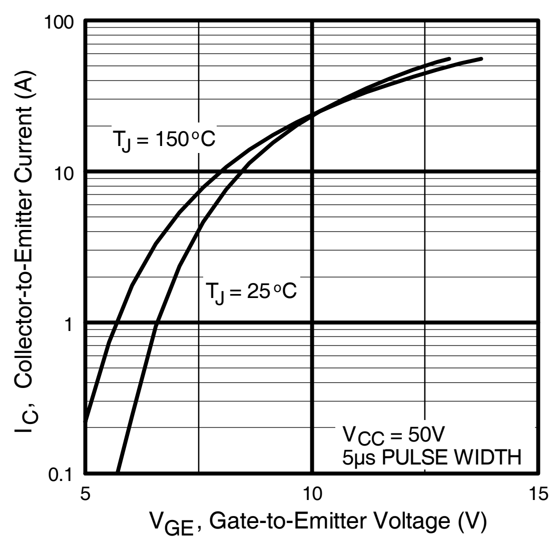


Fig. 3 - Typical Transfer Characteristics

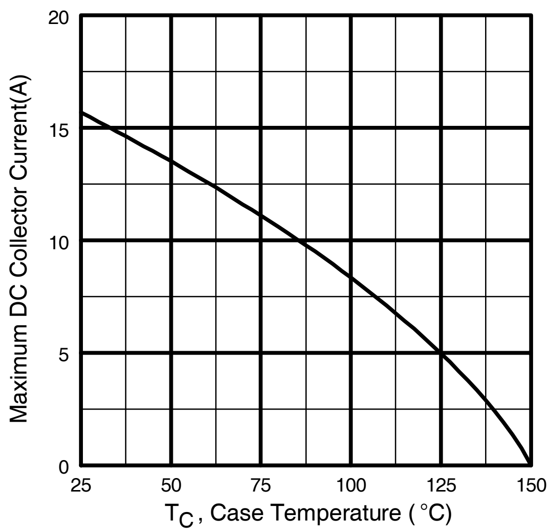


Fig. 4 - Maximum Collector Current vs. Case Temperature

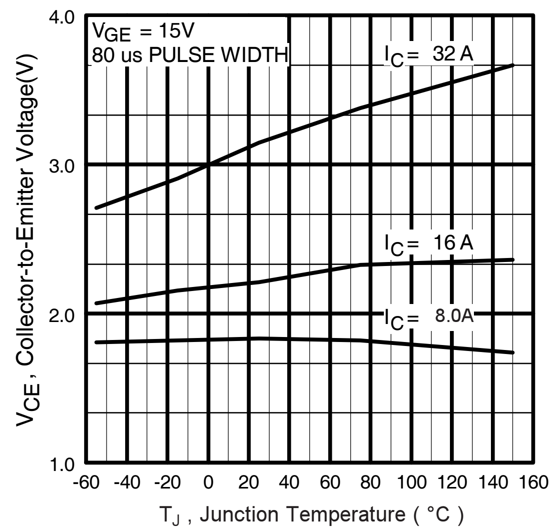


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

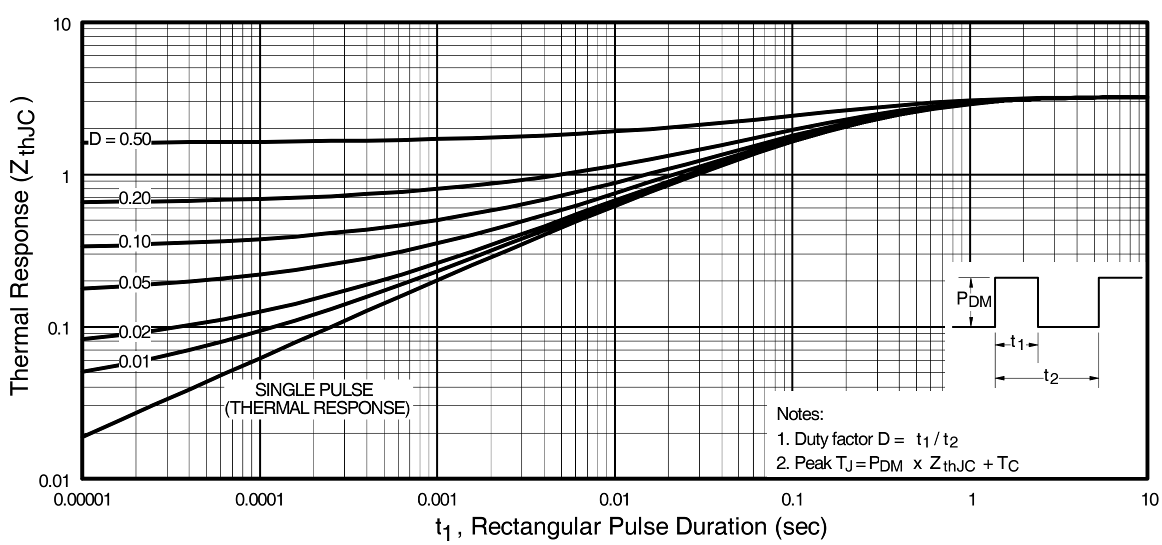


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

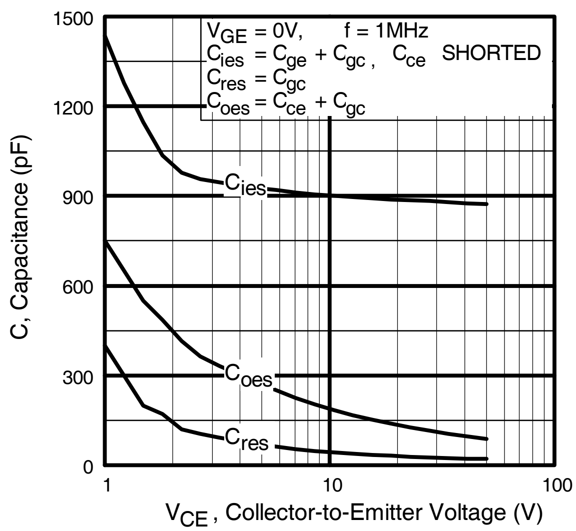


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

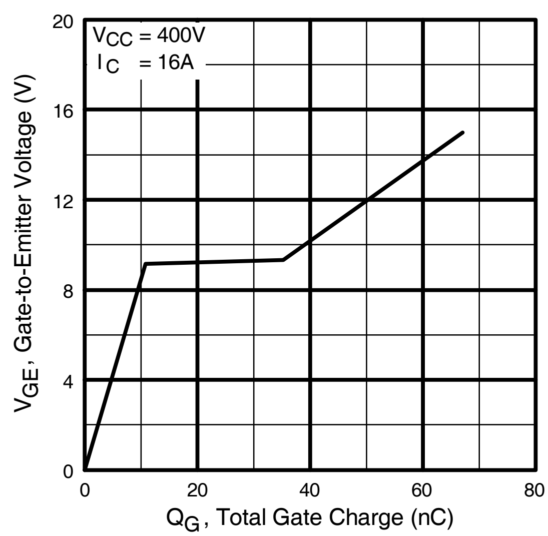


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

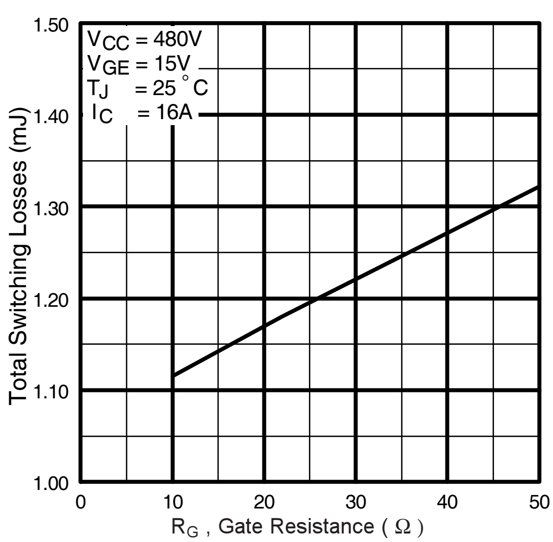


Fig. 9 - Typical Switching Losses vs. Gate Resistance

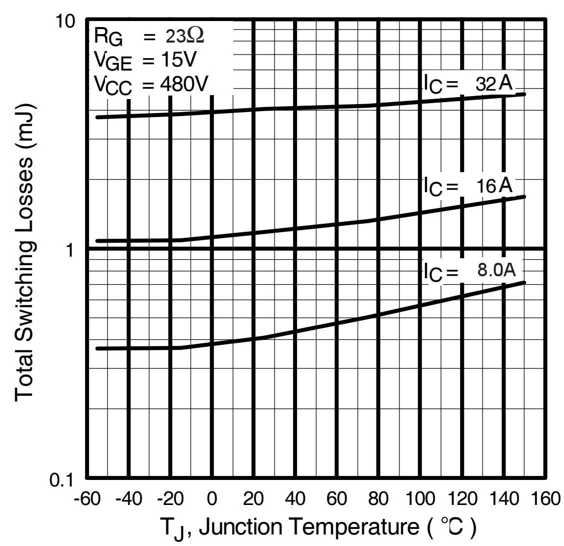


Fig. 10 - Typical Switching Losses vs. Junction Temperature

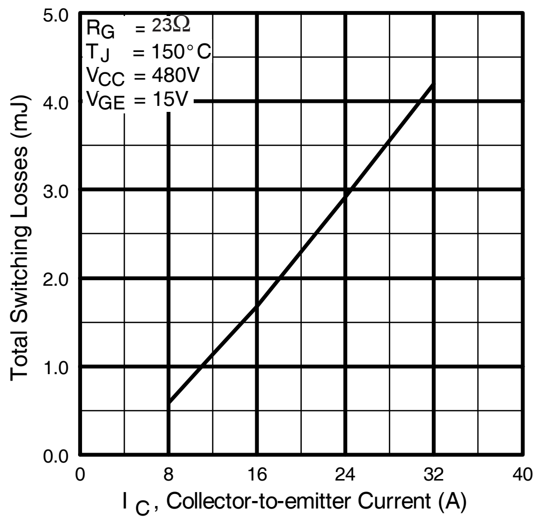


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

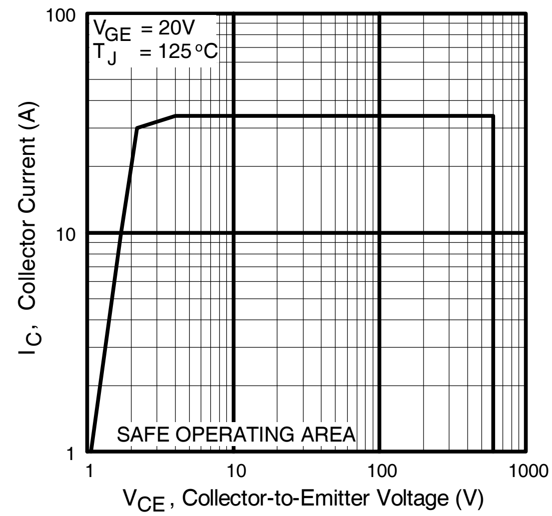


Fig. 12 - Turn-Off SOA

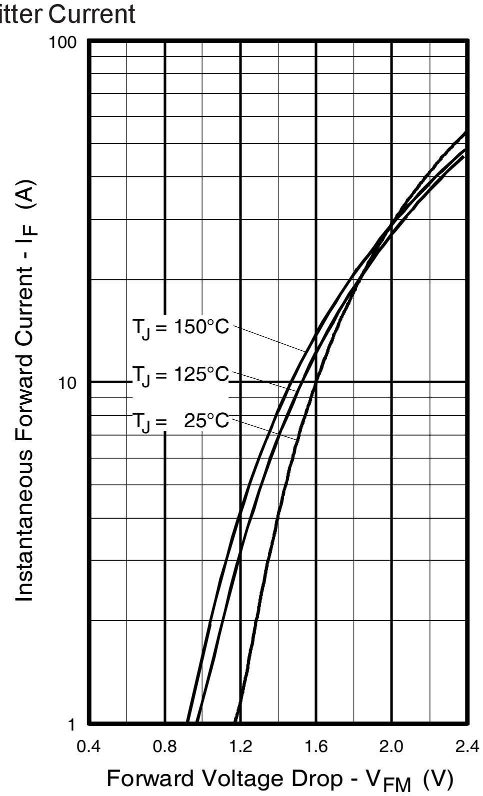


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

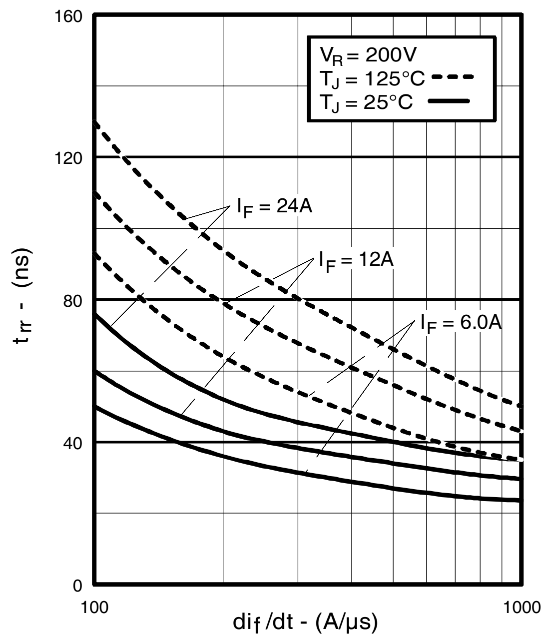


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

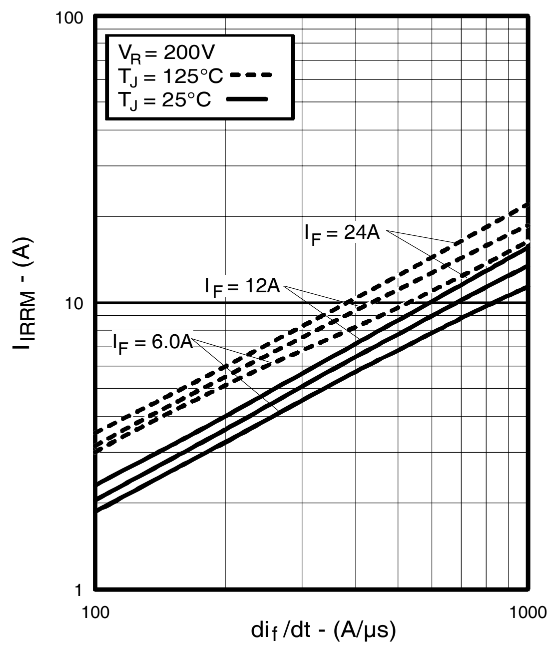


Fig. 15 - Typical Recovery Current vs. di_f/dt

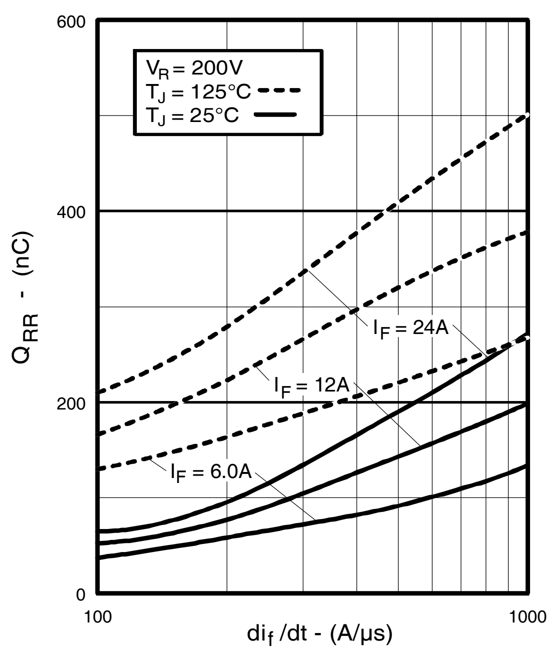


Fig. 16 - Typical Stored Charge vs. di_f/dt

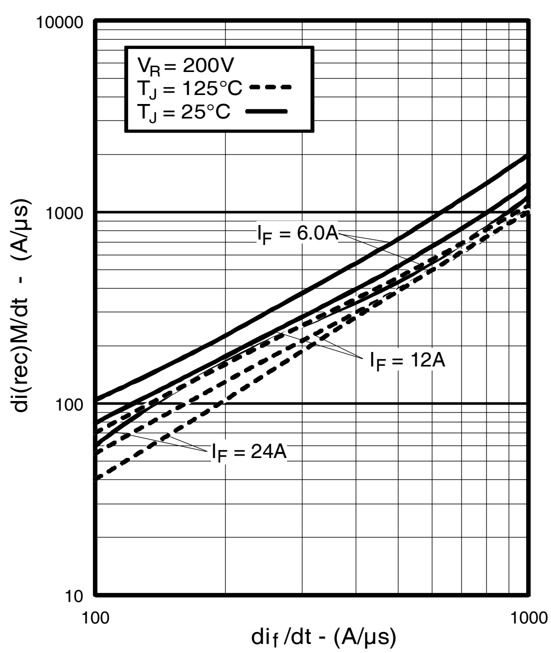


Fig. 17 - Typical $di_{(rec)M}$/dt vs. di_f/dt

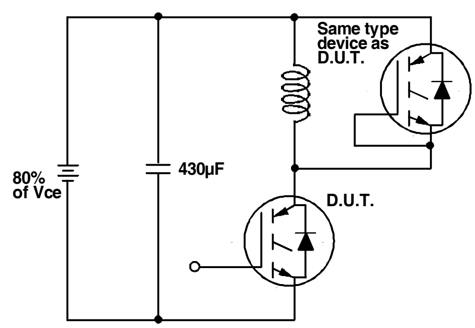


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

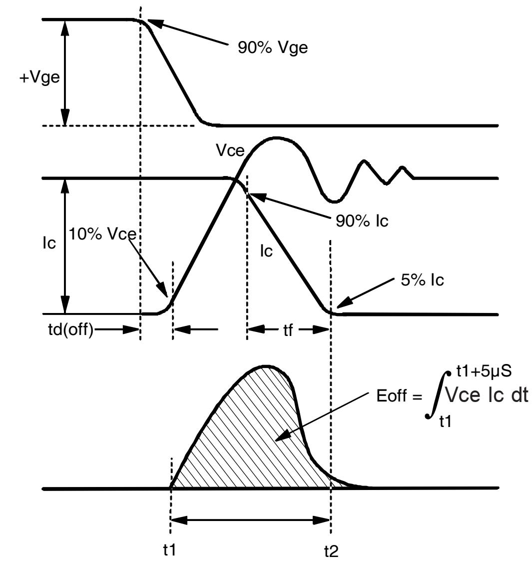


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

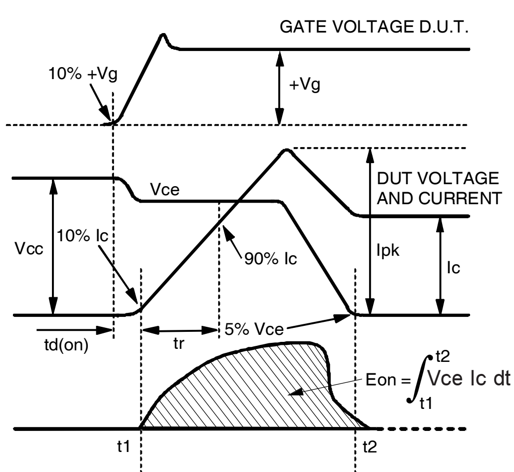


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

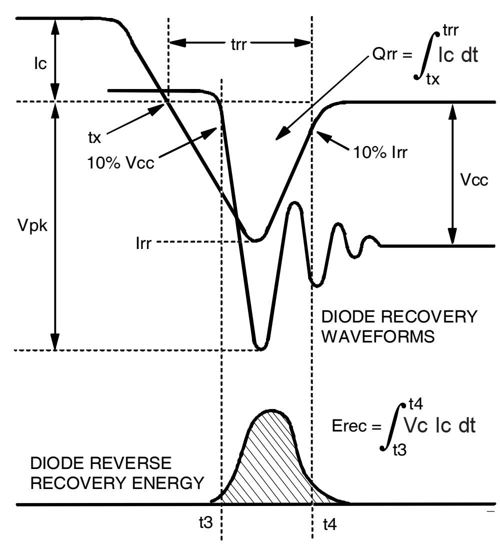


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

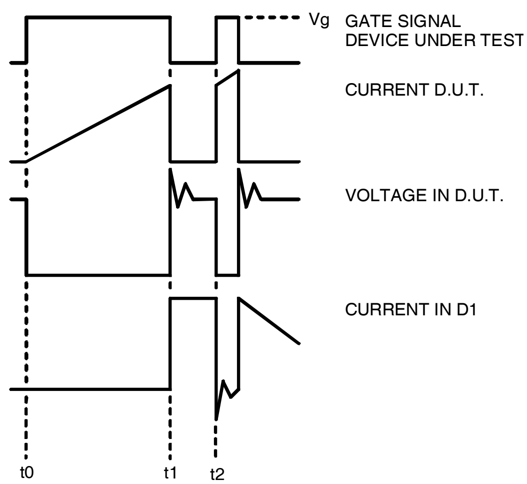


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

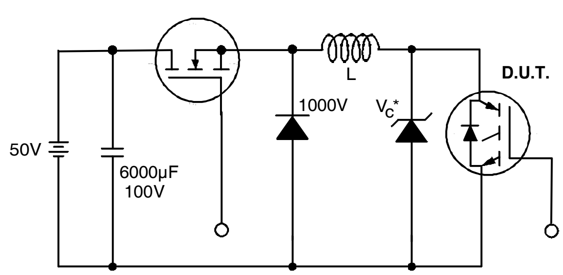


Figure 19. Clamped Inductive Load Test Circuit

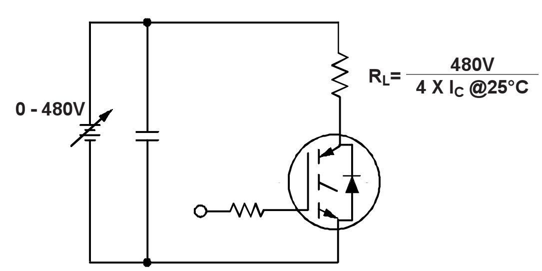


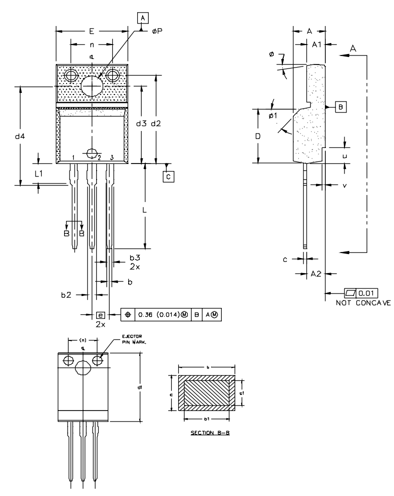
Figure 20. Pulsed Collector Current Test Circuit

Notes:

① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)
② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 23Ω (figure 19)
③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.
④ Pulse width 5.0µs, single shot.
⑤ Uses IRG4BC30KD data and test conditions

TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



NOTES:
1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5.0 DIMENSION b1 APPLY TO BASE METAL ONLY.
6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	0.180	0.190	
A1	2.57	2.83	0.101	0.114	
A2	2.51	2.85	0.099	0.112	
b	0.622	0.89	0.024	0.035	
b1	0.622	0.838	0.024	0.033	5
b2	1.229	1.400	0.048	0.055	
b3	1.229	1.400	0.048	0.055	
c	0.440	0.629	0.017	0.025	
c1	0.440	0.584	0.017	0.023	
D	8.65	9.80	0.341	0.386	4
d1	15.80	16.12	0.622	0.635	
d2	13.97	14.22	0.550	0.560	
d3	12.30	12.92	0.484	0.509	
d4	8.64	9.91	0.340	0.390	
E	10.36	10.63	0.408	0.419	4
e	2.54 BSC		0.100 BSC		
L	13.20	13.73	0.520	0.541	
L1	3.10	3.50	0.122	0.138	3
n	6.05	6.15	0.238	0.242	
øP	3.05	3.45	0.120	0.136	
u	2.40	2.50	0.094	0.098	6
v	0.40	0.50	0.016	0.020	6
ø	3°	7°	3°	7°	
ø1		45°		45°	

LEAD ASSIGNMENTS

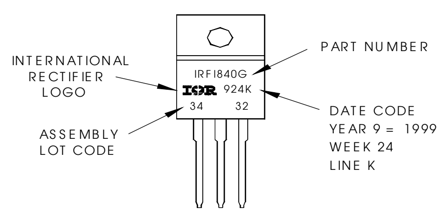
HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK
1.- GATE
2.- COLLECTOR
3.- EMITTER

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24 1999
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International
IOR Rectifier

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Visit us at www.irf.com for sales contact information.07/04

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/